

20. (Twice amended) A method for forming an oxide-nitride-oxide structure in one chamber, the method comprising the steps of:

providing a substrate;

forming a first oxide layer on said substrate, wherein said first oxide layer includes no Cl;

forming a first buffer layer on said first oxide layer;

forming a silicon nitride layer on said first buffer layer;

forming a second buffer layer on said silicon nitride layer; and

forming a second oxide layer on said second buffer layer.